

EAST - [10602890.wsp.1]

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Drafts
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L7: (3080019) (single-electron near transis
L8: (288) (single-electron adj transistor) or
L9: (291) (single-electron adj transistor) or
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DBs: USPAT, US-PGPUB, EPO, JPO

Default operator: OR

Plurals

☒ Highlight all hit terms initially

8 and (spacer\$1)

OK Cancel Image PDF Text HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040142172 A1	20040722	38	Bonded structure including a carbon nanotube	428/403	428/323
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20040119109 A1	20040624	11	Non-volatile memory device having improved programming and erasing	257/315	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20040108529 A1	20040610	29	Single electron device, method of manufacturing the same, and method of	257/288	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20040097023 A1	20040520	22	Method for fabricating semiconductor device with negative differential	438/149	438/151; 438/197
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20040076032 A1	20040422	18	Single electron memory device comprising quantum dots between gate electrode and	365/145	257/E21.209; 257/E29.301
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20040061173 A1	20040401	16	Single-electron transistor and fabrication method thereof	257/347	257/E21.404; 257/E29.322
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20040002195 A1	20040101	12	METHODS AND SYSTEMS FOR FABRICATING NANOPORES FOR	438/301	257/E21.404; 257/E29.322;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20030218163 A1	20031127	15	Emission process for a single photon, corresponding semiconducting device and	257/13	
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20030089899 A1	20030515	162	Nanoscale wires and related devices	257/9	257/E51.04
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20030077625 A1	20030424	39	Partides by facile ligand exchange reactions	435/6	257/E49.001; 435/7.1;
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20020179897 A1	20021205	24	Solid-state quantum dot devices and quantum computing using nanostructured	257/14	

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